



NPN-POWER TRANSISTOR



ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	BU326	BU326A	UNITS	
Collector-emitter voltage (V _{BE} =0)	V _{CES}	800	900	V	
Collector-emitter voltage (open base)	V_{ceo}	375	400	V	
Emitter-base voltage (open collector)	V_{EBO}	10	V		
Collector current	I _c	6	А		
Collector current (peak)	I _{CM}	8	A		
Base current	I _{BM}	3	A		
Total power dissipation up to T _c =95°C	P _{tot}	75	W		
Junction temperature	TJ	200	°C		
Storage temperature	T_{stg}	-65 to 2	°C		

BU326, BU326A TO-3 Metal Can Package





THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNITS
from junction to case	R _{th J-C}	2.33	°C/W

ELECTRICAL CHARACTERISTICS (T_A =25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS			826A		
PARAIVIEIER	STWBUL	TEST CONDITIONS	MIN	MAX	MIN	MAX	
		V _{BE} = 0, V _{CE} = 800V	-	1.0	-	-	-
		V _{BE} = 0, V _{CE} = 900V	-	-	-	1	
Collector cut-off current	I _{CES}	V _{BE} = 0, V _{CE} = 800V, T _C =125°C	-	2	-	-	mA
		V _{BE} = 0, V _{CE} = 900V, T _C =125°C	-	-	-	2	
Collector -emitter sustaining voltage	$V_{CEO(sus)}^{*}$	I _c =100mA, I _B =0	375	-	400	-	V
Collector -emitter voltage	V_{CES}	I _c =1mA, V _{BE} = 0	800	-	900	-	V
Emitter-base voltage	V_{EBO}	I _E =10mA, I _C =0	10	-	10	-	V
Collector-emitter saturation voltage	V _{CEsat} *	I _C = 2.5 A, I _B = 0.5 A	-	1.5	-	1.5	V
Base-emitter saturation voltage	V _{BEsat} *	I _C = 2.5 A, I _B = 0.5 A	-	1.4	-	1.4	V
Collector-emitter saturation voltage	V _{CEsat} *	I _c = 4 A, I _B = 1.25 A	-	3.0	-	3.0	V
Base-emitter saturation voltage	V _{BEsat} *	I _C = 4 A, I _B = 1.25 A	-	1.6	-	1.6	V
D.C. Current gain	h _{FE} *	I _C = 1 A , V _{CE} = 5V	typ. 25				

* Pulsed: pulse duration = 300 µs; duty cycle = 1.5%







	DIM	MIN.	MAX.
	Α	_	39.37
	В	_	22.22
	С	6.35	8.50
	D	0.96	1.09
	E	_	1.77
	F	29.90	30.40
mm	G	10.69	11.18
⊒.	Η	5.20	5.72
ions	J	16.64	17.15
All dimensions in mm.	K	11.15	12.25
	L	_	26.67
All	М	3.84	4.19



PIN CONFIGURATION 1. BASE 2. EMITTER 3. COLLECTOR

Packing Detail

PACKAGE	STAND	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	GrWt	
TO-3	100 pcs/pkt	1.3 kg/100 pcs	12.5" x 8" x 1.8"	0.1K	17" x 11.5" x 21"	2K	27.5 kgs	





Customer Notes:

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.

2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

DISCLAIMER

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end product), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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